

Application No.: 10/702,372

Docket No.: JC-7897-D

REMARKS**Present Status of the Application**

Claims 39 and 46-50 are presently rejected. Specifically, claims 39 and 46-50 are rejected under 35 U.S.C. 102(b) as been anticipated by Voldman et al. (US Patent No.6,015,993). Applicants have amended independent claims 39 and 46. After entry of the amendments, claims 39 and 46-50 remain pending in the present application, and reconsideration of those claims is respectfully requested.

Discussion of Office Action Rejections

The Office Action rejected claims 39 and 46-50 under U.S.C. 102(b) as being anticipated by Voldman et al. (US Patent No.6,015,993). Applicants respectfully traverse the rejection for at least the reasons set forth below.

As amended, dependent claim 39 recites:

39. A method of forming a non-gate diode of a SOI, comprising:

...forming a lightly doped region in the well region, the lightly doped region comprising a lightly doped P-type region and a lightly doped N-type region directly connected to the lightly doped P-type region;

In re Voldman, as shown in fig 7, the light doped n-type region 144 and a light doped p-type region 142 are separated by edge implants 174, 172 and implanted well 152. *In other words, light doped n-type region 144 is not directly connected to the lightly doped P-type region 142.* Therefore, claim 39 as currently amended should not be considered as being anticipated by Voldman et al. US Patent 6,015,99 or any of the other cited references, taken alone or in combination, and is submitted as allowable.

As amended, dependent claim 46 recites:

46. A method of forming a non-gate diode in a CMOS process, comprising:

...forming a pair of second type doped regions located in the well region wherein the pair of second type doped regions are adjacent to the blocking isolation structure respectively, and each second type doped region is separated from the first type doped region by the well.

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In re Voldman, as shown in fig 7, the n-type region 164 is adjacent to the blocking isolation structure while the light doped n-type region 144 is adjacent to the n-type region 164 but not the blocking isolation structure. *In other words, light doped n-type region 144 and n-type region 164 are not adjacent to the blocking isolation structure respectively.* Therefore, claim 46 should not be considered as being anticipated by Voldman et al. US Patent 6,015,99 or any of the other cited references, taken alone or in combination, and is submitted as allowable.

If independent claim 46 is allowable over the prior art of record, then its dependent claims 47-50 are allowable as a matter of law, because these dependent claims contain all features of their respective independent claim 46. *In re Fine*, 837 F.2d 1071 (Fed. Cir. 1988).

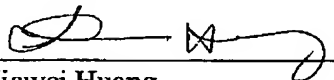
CONCLUSION

For at least the foregoing, it is believed that the pending claims are in proper condition for allowance. If the Examiner believes that a telephone conference would expedite the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

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Respectfully submitted,
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